

IN THE SPECIFICATION:

Please amend the section title appearing directly above paragraph number [0001] as follows:

~~CROSS-REFERENCE~~ CROSS-REFERENCE TO RELATED APPLICATION

Please amend paragraph number [0006] as follows:

[0006] The present invention provides apparatus, systems and methods relating to the reconstruction of semiconductor wafers for wafer-level processing. Selected semiconductor dice having alignment cavities formed in a surface, such as the ~~rear~~ lower surface, thereof are placed in contact with alignment droplets of a material in a liquid, gel or other flowable state, which position the dice through surface tension interaction. Selected dice may be dice without known defects qualified during probe testing or dice recovered from damaged wafers. The alignment droplets may be disposed in a pattern corresponding to that of the alignment cavities on a reconstruction table, or on a fixture plate. The alignment droplets are solidified to maintain the die positioning and an underfill is disposed about the solidified alignment droplets to strengthen and maintain the reconstructed wafer. Where present, the fixture plate may add additional strength and simplify processing steps by providing structure for enhanced handling of the reconstructed wafer. The reconstructed wafer may undergo any desired wafer-level processing although the present invention is especially suitable for enhancing the utility of wafer-level testing and burn-in equipment used to qualify dice as “known good dice” or KGD. Where the alignment droplets are composed of sacrificial material, or the alignment cavities contain sacrificial material, this material may be removed from the reconstructed wafer. The resulting voids can be filled to form interconnects on the resulting dice. Where the voids are filled with conductive material, contact pads, connections or bumps may be formed.

Please amend paragraph number [0008] as follows:

[0008] FIG. 1 is a side view of ~~one possible~~ an alternative embodiment of a reconstruction table and fixture plate, useful with some embodiments in accordance with the present invention;

Please amend paragraph number [0012] as follows:

[0012] FIG. 5 is a side view showing one embodiment of a reconstructed ~~wafer~~ wafer, in accordance with the present ~~invention~~ invention, separated from the reconstruction table;

Please amend paragraph number [0019] as follows:

[0019] FIG. 12 is a side view showing one embodiment of a reconstructed ~~wafer~~ wafer, in accordance with the present ~~invention~~ invention, separated from the reconstruction table;

Please amend paragraph number [0021] as follows:

[0021] FIG. 13 is a side view depicting the reconstructed wafer of FIG. 12 after a ~~back-grinding~~ back-grinding process;

Please amend paragraph number [0027] as follows:

[0027] Turning to FIG. 1, there is depicted a reconstruction table 100. Reconstruction table 100 may be used as a platform for reconstructing a semiconductor wafer. One or more wafer reconstruction locations 101 may be present on the reconstruction table 100. In other words, a reconstruction table 100 may be configured for concurrent reconstruction of multiple wafers. A temperature control system 102, schematically represented by coils, may be present in connection with reconstruction table 100 and used to raise, lower, or maintain a desired temperature of the reconstruction table 100 and surrounding environment. In practice, temperature control system 102 may comprise resistive heating elements, passageways within reconstruction table 100 for circulating fluid of heating or cooling, semiconductor-type heat exchange modules, or other heat exchange systems known in the art. Further, one or more

sensors 103 may be placed within ~~(as shown)~~ reconstruction table 100 or in contact therewith, sensors 103 being used with a controller 107 for modulating the temperature of reconstruction table 100 in each region or portions thereof.

Please amend paragraph number [0028] as follows:

[0028] At each reconstruction location 101, a plurality of patterns of alignment vias 104 open out at the top surface of a substrate 114 comprising reconstruction table 100, each in communication with an alignment material delivery system 105. ~~A- Substrate 114 may include a~~ fixture plate 110 ~~may be~~ disposed on the reconstruction table 100. Fixture plate 110 has a plurality of patterns of vias 106 that align with the alignment vias 104 when placed on a reconstruction location 101 on reconstruction table 100. Fixture plate 110 may be formed of any suitable material, including polymeric materials, crystalline silicon, glass, steel, aluminum or any other suitable material known to those of ordinary skill in the art and desirable for the processing involved. For example, where subsequent processing steps require the ~~rear~~ lower surface of a wafer to be silicon, a silicon fixture plate 110 may be selected. ~~Alternate-~~ Alternative embodiments of the process may occur without the use of a fixture plate 110. For example, a resulting wafer lacking a fixture plate 110 may be removed from the reconstruction table 100 following ~~underfill (which will be discussed below)-~~ underfill, the discussion of which follows below. To facilitate such a procedure, the reconstruction location 101 may be coated with a compound to aid in the release of a completed wafer therefrom.

Please amend paragraph number [0029] as follows:

[0029] As shown in FIG. 2, using an alignment material delivery system 105, an alignment material 108 is delivered in a liquid, gel or other flowable state through at least one alignment via 104 ~~(and and corresponding via 106 of fixture plate 110 where present)-~~ when present, to form at least one alignment droplet 112 at the reconstruction location 101, atop the fixture plate 110 ~~where~~ when present. ~~Desirably,~~ Preferably, a number of alignment

droplets 112 will be formed into a desired pattern by the arrangement of a number of alignment vias 104, as will be explained in more detail further herein.

Please amend paragraph number [0030] as follows:

[0030] Turning to FIG. 3, a plurality of semiconductor dice 120 are shown disposed at the reconstruction location 101. Dice 120 may be selected by qualification using wafer probe testing, visual inspection of dice sites on a wafer, or as otherwise desired and known to those of ordinary skill in the art. Each die 120 may be formed of silicon, gallium arsenide, indium phosphide or other suitable semiconductor material and includes at least one alignment cavity 122 and preferably a pattern thereof, located on a ~~rear- lower~~ surface ~~123 thereof. 123.~~ For purposes of facilitating the understanding of the invention, the die 120 will be referred to as having an active surface 121 as the ~~“front”~~ upper surface of the die with an opposite ~~rear- lower~~ non-active surface 123. It will be understood that such terms are for making relative positions clear and do not limit the invention. Alignment cavities 122 may be formed in the ~~rear- lower~~ surface 123 of each die 120 using any suitable method for forming vias, cavities, or trenches in semiconductor substrates known to those of ordinary skill in the art. For example, the alignment cavities 122 may be formed by wet etching, dry etching (and comprise either isotropic etching or anisotropic etching), laser ablation, drilling or boring with a mechanical drill bit, or otherwise as known to those of ordinary skill in the art. Although embodiments utilizing a single alignment cavity 122 may be designed and are within the scope the present invention, it is currently preferred to use a plurality of patterns of alignment cavities 122 on the ~~rear- lower~~ surface 123, in order to allow the die 120 to be correctly positioned in multiple directions, being the X and Y directions parallel to the plane of reconstruction table ~~400- 100,~~ as well as rotationally in the same plane. For example, one or more parallel rows of alignment cavities 122 or a pattern of alignment cavities 122 (for example, patterns of four cavities in each die 120 to be aligned) may be formed on the ~~rear- lower~~ surface of each die. It will be appreciated that any desirable or advantageous arrangement of the alignment cavities 122 on the ~~rear- (non-active)- lower~~

non-active surface 123 of the die 120 may be used and all such patterns and arrangements are within the scope of the present invention.

Please amend paragraph number [0031] as follows:

[0031] Each alignment cavity 122 may be formed to any desired depth in the die 120, so long as it is sufficient to enable the alignment of the die 120 when interacting with a corresponding alignment droplet 112, as will be explained further herein. For some embodiments, one or more alignment cavities 122 may be used as vias connecting the active surface 121 of the die 120 to the ~~rear~~ non-active surface 123, increasing throughput by using a single structure for multiple purposes, and enabling novel methods of forming die 120 interconnects or bumped dice for flip-chip applications. Such embodiments will be discussed in more detail further herein.

Please amend paragraph number [0032] as follows:

[0032] As a die 120 is placed into the reconstruction location 101 by, for example, conventional and suitably programmed ~~pick-and-place~~ pick-and-place equipment, it is roughly aligned with a desired final position in the resulting reconstructed wafer. The alignment droplet(s) 112 thus make contact with one or more alignment cavities 122 on the ~~rear~~ non-active surface 123 of the die 120. The die 120 is then released and the surface tension of the alignment droplets 112 interacts with the similarly patterned alignment cavities 122 to position the die 120 in its final, precise alignment and hold the die 120 in the correct, desired position. By positioning patterns of alignment droplets 112 in the reconstruction location 101 to define locations of dice 120 for reconstruction of a wafer, a plurality of dice 120 may be aligned in proper positions with respect to one another to form a reconstructed wafer for further wafer-level processing. Achieving and maintaining proper positioning among the dice is important and required to allow processing of the reconstructed wafer to take place with conventional equipment.

Please amend paragraph number [0033] as follows:

[0033] Once a desired number of dice 120 are correctly aligned in the proper positions, the alignment droplets 112 are then at least partially solidified to retain the dice 120 in the correct positions. For example, by using the temperature control system 102, the temperature of the reconstruction table 100 may be raised or lowered to effect an at least partial solidification of a liquid alignment material 108 comprising alignment droplets 112, solidifying the liquid alignment material 108 and adhering the solidified alignment droplets 112 to the dice 120. ~~For~~ In an alternative example, when using a thermoplastic resin such as the alignment material 108, the thermoplastic resin may be heated to ~~melt~~ a melting point by using temperature control 102 and delivered through alignment vias 104 to form alignment droplets ~~112, following which the~~ 112. The temperature of the thermoplastic resin may then be cooled or allowed to cool to a point where the alignment material 108 at least partially solidifies. As another example, a thermoset resin may be used as the alignment material 108, pumped through the alignment vias 104 to form alignment droplets 112 and then heated using temperature control system 102 to solidify. A third exemplary alignment material 108 may be a liquid epoxy that is heat cured to solidify. With such embodiments, where necessary, the temperature of the alignment vias 104 may be separately maintained at a lower level to prevent solidification therein. An additional example of a suitable alignment material may be a low melting point metal, such as a tin/lead solder, silver solder or other low melting point metals or alloys. The low melting point metal may be melted and delivered through alignment vias 104 to form alignment droplets 112 and then cooled, or allowed to cool, to solidify. It will, of course, be appreciated that alternative processes for solidifying alignment droplets 112 may be used and are within the scope of the present invention, such as the application of a chemical setting agent, the exposure of alignment droplets 112 formed of a photoreactive alignment material 108 to an appropriate wavelength of light, such as a photopolymer ~~curable using that is cured by~~ exposure to radiation (as, for example, polymers that are liquid when heated and gel upon exposure to radiation, such as UV light, x-rays, microwaves, etc.), or any other process known to those of ordinary skill in the art.

Please amend paragraph number [0034] as follows:

[0034] Once alignment droplets 112 are at least partially solidified, an underfill material 126, such as an epoxy, may be disposed under the dice 120. The embodiment of ~~FIG. 3,~~ FIG. 3, with an underfill material 126 disposed between the dice 120 and the fixture plate 110, is shown in FIG. 4. Various dielectric underfill materials 126, such as conventional underfill epoxies, are known to those of ordinary skill in the art and any suitable underfill material may be employed to retain the die 120 to the fixture plate 110 or otherwise solidify the positions of dice 120 in the reconstructed wafer. Once the underfill material 126 has cured, a reconstructed wafer 130 is formed and may be removed with fixture plate 110 (~~if-used~~) present from the reconstruction table 100, as shown in FIG. 5. The reconstructed wafer 130 then may undergo any desired wafer-level processing to complete the fabrication of the dice 120 or for creation of complete multidie semiconductor assemblies. For example, the reconstructed wafer 130 may undergo wafer-level testing and burn-in to qualify dice 120 thereof as KGD, although it will be appreciated that any desired wafer-level treatment such as wafer-level rerouting or wafer-level treatments for packaging may be performed on the reconstructed wafer 130.

Please amend paragraph number [0035] as follows:

[0035] It will be appreciated that the term “reconstructed wafer,” as used herein, means any reconstructed bulk-~~substrate~~ substrate, including semiconductor dice. Such reconstructed wafers may have any desired shape, including a conventional round wafer shape, which may be desirable for processing with conventional wafer handling and processing equipment. Other embodiments may produce square or rectangular reconstructed wafers, which may be desirable for use with testing equipment. All such shapes are within the scope of the present invention.

Please amend paragraph number [0036] as follows:

[0036] Once wafer-level processing is complete, the reconstructed wafer 130 may then be singulated into a number of separate dice 120, which may be KGD, as previously noted. One process for singulation is depicted in FIGS. 6, 7 and 8. The reconstructed wafer 130 is attached

to a film of adhesive-coated polymer 132, as in a conventional wafer back-grinding process, with the active surface 121 of the dice 120 adhered to the adhesive-coated film 132, as depicted in FIG. 6. The reconstructed wafer 130 is then back-ground, removing the fixture plate 110 (~~where~~ (when present)), the underfill material 126 and the alignment ~~drops~~ droplets 112. Where the dice 120 are of sufficient depth or thickness, the back-grinding may continue to remove the alignment cavities 122 and the remainder of alignment droplets 112 located therein and any desired portion of the reconstructed wafer 130 thickness, resulting in the structure shown in FIG. ~~7 of a number 7~~, of a plurality of thinned dice 120 attached to the adhesive-coated film 132. The individual finished dice 120 may then be separated by simply removing the adhesive-coated film 132, as depicted in FIG. 8. Of course, it will be appreciated that any alternative method for wafer singulation known to those of ordinary skill in the art may be used to separate the dice 120. For example, the reconstructed wafer may be singulated with a conventional wafer saw or by any other suitable technique.

Please amend paragraph number [0038] as follows:

[0038] Some embodiments of processes in accordance with the present invention may be used to form interconnects or other structures as a reconstructed wafer is formed or dice 120 are singulated therefrom. Examples of such processes are depicted in FIGS. ~~9 through 18~~ 9-18, as discussed below.

Please amend paragraph number [0039] as follows:

[0039] FIG. 9 depicts several different dice 220A, 220B and 220C that may be used in practicing certain embodiments of the present invention. Different alignment via 222 treatments have been applied to each die 220A, 220B and 220C. The alignment vias 222 of die 220A comprise at least one via 222A that passes through the thickness of the entire die, allowing contact between the active surface 221 and the ~~rear~~ non-active surface 223 therethrough. Where desirable, a suitable coating may be placed on the interior surface of the via 222A. For example, an insulative coating may be placed on the via 222A walls to protect the die 220A from the



inductive effects of a current passing through conductive material later filling the via 222A. Alternatively, a conductive coating may be applied to form part of a conductive interconnection structure.

Please amend paragraph number [0040] as follows:

[0040] The alignment vias 222 of die 220B similarly comprise at least one via 222B that passes through the thickness of the die 220B. Via 222B is partially filled with a selected filler material 225, such as a sacrificial material or a conductive material that can be in electrical communication with the integrated circuit formed on the active surface 221 of the die 220B. ~~Desirably,~~ Preferably, via 222B is filled from 1/4 to 3/4 with the selected filler material 225, although any other suitable partial filling may be used. Similarly, the at least one alignment via 222C of die 220C passes through the thickness of the die 220C, but is filled with any suitable selected filler material 225 substantially throughout its depth. It will, of course, be appreciated that the walls of alignment holes 222B and 222C may be coated with any desired coatings prior to filling with the selected filler material 225.

Please amend paragraph number [0041] as follows:

[0041] As shown in ~~FIG.~~ FIGS. 9 and 10, a number of alignment droplets 112 are extruded through the reconstruction table 100, and the dice 220A, 220B, ~~220C~~ 220C, are disposed thereon, such that the interaction of the surface tension of the alignment droplets 112 aligns dice 220A, 220B, ~~220C~~ 220C, for exact placement in a reconstructed wafer, as has been discussed previously herein. It will be appreciated that the alignment droplet 112 size may be controlled to result in filling the volume of the alignment vias 222A-222C that has not been filled previously with a selected filler material with the alignment droplet 112. In the case of an “empty” via, such as 222A, this can result in a via filled with the alignment material 108 or a via partially filled with alignment material 108. For a partially empty via, such as 222B, this results in a via partially filled with selected filler material 225 with the remainder filled by alignment material 108. In the case of a filled alignment via 222C, the material of the alignment

material 108 is selected to “wet” ~~to the~~ the filler material 225, so that the surface tension of alignment droplets 112 is effective to align die 220C. Where desired, the alignment material 108 may be a conductive material, such as a metallic solder, a conductive polymer, or a polymer containing conductive material suspended therein. Alternatively, the alignment material 108 may comprise a sacrificial material. It will be appreciated that the term “~~sacrificial material~~” ~~as used herein~~ material,” as used herein, refers to any material, or compound, that may be utilized for a specific function in any process or method of the present invention and then be removed at a later stage of such process or method. For example, where the alignment droplets 112 are back-ground from the die 120, as discussed previously herein, such alignment droplets 112 are considered to be a sacrificial material. Sacrificial materials may be selected to facilitate their removal after use, as will be discussed further herein.

Please amend paragraph number [0042] as follows:

[0042] The alignment droplets 112 are then heated, cooled, or otherwise treated to at least partially solidify and an underfill material 126 is disposed underneath the dice 220A, 220B, ~~220C~~ 220C, and around the solidified alignment droplets 112, resulting in the structure seen in FIG. 11. Once the underfill 126 has set or otherwise solidified, the reconstructed wafer 230 may then be removed for ~~processing~~ processing, as discussed previously herein and depicted in FIG. 12. ~~An elevated~~ A plan view of a portion of the reconstructed wafer 230 is shown in FIG. 12A.

Please amend paragraph number [0043] as follows:

[0043] ~~At this point,~~ Referring back to FIG. 12, the reconstructed wafer 230 may undergo any wafer-level processing that is desired as is discussed previously herein. Wafer-level burn-in and testing may even be conducted. Where the alignment material 108 selected is a conductive material and, if present, the selected filler material 225 is also conductive and makes contact with the patterns of the active surface 221 of the die ~~220a,~~ 220A, 220B, 220C, testing and burn-in may be effected by making electrically communicative contact with the solidified

alignment material 108 as exposed at the ~~rear~~ non-active surface 223 of the reconstructed wafer 230, as through the vias 106 of a fixture plate 110.

Please amend paragraph number [0044] as follows:

[0044] Following the wafer-level processing, the reconstructed wafer 230 may then be singulated into a ~~number~~ plurality of separate dice 220A, 220B, 220C. Similar to that discussed previously herein, one process for doing so is depicted in FIGS. 13 and 14. The reconstructed wafer 230 is attached to a length of adhesive-coated film 132, as in a conventional wafer back-grinding process, with the active surfaces 221 of the dice 220A, 220B, ~~220C~~ 220C, adhered to the adhesive-coated film 132. The reconstructed wafer 230 is then back-ground, removing the fixture plate 110 (where present), the underfill material 126 and the alignment material 108 or selected filler material 225 that is present in the portion of the dice 220A, 220B, ~~220C~~ 220C, that are back-ground. This results in a number of thinned dice 220A, 220B, ~~220C~~ 220C, attached to the adhesive-coated film 132, similar to that depicted in FIG. 7. Each finished die 220A, 220B, ~~220C~~ 220C, contains a via 222A, 222B, ~~222C~~ 222C, across the width thereof that is filled either with the selected filler material 225 or the alignment material 108. Where the alignment material ~~108~~ 108, alone or in combination with a contacting selected filler material ~~225~~ 225, is conductive and is in electrical communication with the active surface 221 of the dice 220A, 220B, 220C, this provides contacts 226 on the ~~rear~~ non-active surfaces 223 of the dice that may be utilized in mounting the dice 220A, 220B, ~~220C~~ 220C, in a complete semiconductor package or in an appropriate device. Individual finished dice 220A, 220B, ~~220C~~ 220C, may be separated by simply removing the adhesive-coated film 132, as depicted in FIG. 14. Of course, it will be appreciated that any alternative method for wafer ~~singulation~~ singulation, known to those of ordinary skill in the ~~art~~ art, may be used to separate the dice 220A, 220B, 220C.

Please amend paragraph number [0045] as follows:

[0045] Some additional processing embodiments, in accordance with the principles of the present invention, are depicted in FIGS. ~~15 through 18.~~ 15-18. A reconstructed wafer 230A is created as discussed previously herein in connection with FIGS. ~~9 through 12.~~ 9-12. At this point, the reconstructed wafer may undergo any desired wafer-level processing procedure. Then, if a fixture plate 110 was used in creating the reconstructed wafer 230A, the fixture plate 110 is removed, mechanically by ~~back-grinding~~ back-grinding, or by ~~forming~~ utilizing the fixture plate 110 formed from a material that may be ~~dissolved~~ dissolved, or by removing the fixture plate 110 with treatment by a suitable release agent. Of course, the need for this procedure may be eliminated by creating the reconstructed wafer 230A that lacks a fixture plate 110.

Please amend paragraph number [0047] as follows:

[0047] Once the sacrificial material is removed, the reconstructed wafer 230A contains at least one void 240 in the underfill material 126 that corresponds to a removed alignment droplet 112 and may be connected to an empty, or at least partially-empty ~~empty~~, alignment via, such as those depicted as 222A and 222B in FIG. 15. At this point, the vacated volume may be filled with a selected replacement filler material 242, as is desired. For example, the selected replacement filler material 242 may be a conductive metal or alloy, such as tin/lead solder, gold or a conductive polymer or conductively filled polymer to create a conductive structure through the ~~via~~ vias 222A, 222B, ~~222C~~ 222C, and an integral conductive bump 244 on the ~~rear~~ non-active surface 223, as depicted in FIG. 16. Of course, it will be appreciated that any desired selected replacement filler material 242 may be used.

Please amend paragraph number [0048] as follows:

[0048] The reconstructed wafer 230A may then undergo any additional desired wafer-level processing. It may be advantageous to attach the active surface 221 of the reconstructed wafer 230A to a length of adhesive-coated film 132 to protect the active surfaces 221 of the dice 220A, 220B, 220C, as depicted in FIG. 17. This procedure may occur

during processing, or prior to removal of the sacrificial material. Processing of the wafer at this stage may include wafer testing and burn-in of the dice 220A, 220B, ~~220C~~ 220C, using conductive bumps 244 as contacts.

Please amend paragraph number [0049] as follows:

[0049] The underfill material 126 may then be removed from the reconstructed wafer to substantially fully expose the conductive bumps 244. This may be accomplished in any suitable manner, such as by selectively removing the underfill material 126 through a chemical etch process, or by selecting an underfill material that can be induced to reflow from the reconstructed wafer 230A under appropriate conditions. Removal of the underfill material results in dice 220A, 220B, ~~220C~~ 220C, with substantially fully exposed bumps ~~244~~ 244, similar to those depicted in FIG. 18. Of course, it will be appreciated that some embodiments in which the underfill material is not removed may be utilized and are within the scope of the present invention.

Please amend paragraph number [0050] as follows:

[0050] The individual dice 220A, 220B, ~~220C~~ 220C, may be singulated from the reconstructed wafer 230A. Where the underfill material 126 has been removed, similar to the embodiment depicted in FIG. 18, this may be accomplished by removing the dice 220A, 220B, ~~220C~~ 220C, from the adhesive-coated film 132, as has been discussed previously herein. Alternatively, singulation of the reconstructed wafer 230 may be accomplished using wafer sawing techniques. Where adhesive-coated film 132 has been applied to the active surface 221 of the reconstructed wafer 230A, this leaves a protective layer on the active surfaces 221 of the resulting dice 220A, 220B, 220C. Alternatively, singulation may not be effected and the dice 220A, 220B, ~~220C~~ 220C, may be marketed or used as multichip assemblies. Of course, an adhesive-coated film 132 that is susceptible to chemical etching or other non-mechanical severance or removal may be used and such singulation is also within the scope of the present invention.

Please amend paragraph number [0051] as follows:

[0051] Using the processes, equipment and methods in accordance with the present invention, reconstructed wafers 230 and 230A can be created that may include only known good dice. These reconstructed wafers may then be processed in the same manner as any other wafer, using standard wafer-level processing equipment.